EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	1	("20070141783").PN.	US-PGPUB; USPAT	OR	OFF	2009/03/30 07:23
L7	0	steven adj t adj peake	US-PGPUB; USPAT	OR	ON	2009/03/30 07:28
L8	40	steven with t with peake	US-PGPUB; USPAT	OR	ON	2009/03/30 07:29
L9	33	8 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2009/03/30 07:29
L10	21	steven with t with peake	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/30 07:32
L11	11310	trench near5 (fet or transistor or mosfet)	US-PGPUB; USPAT	OR	ON	2009/03/30 07:34
L12	8033	11 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2009/03/30 07:34
L13	1271	12 and (p with n with junction)	US-PGPUB; USPAT	OR	ON	2009/03/30 07:34
L14	582	13 and body and drain	US-PGPUB; USPAT	OR	ON	2009/03/30 07:35
L15	467	14 and concentration	US-PGPUB; USPAT	OR	ON	2009/03/30 07:35
L16	1638	trench adj (fet or transistor or mosfet)	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
L17	1181	L16 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
L18	1002	L17 and (gate with trench)	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
L19	188	L18 and (p near3 n with junction)	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
L20	181	L19 and drain	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
L21	352	15 not 20	US-PGPUB; USPAT	OR	ON	2009/03/30 07:37
S1	1	("6160288").PN.	US-PGPUB; USPAT	OR	OFF	2008/09/26 14:12
S2	20422	insulated near3 gate with transistor	US-PGPUB; USPAT	OR	ON	2008/09/26 18:00
S3	3657	S2 and trench	US-PGPUB; USPAT	OR	ON	2008/09/26 18:01
S4	2406	S3 and diffusion	US-PGPUB; USPAT	OR	ON	2008/09/26 18:01
S5	435	S4 and (p near3 n near3 junction)	US-PGPUB; USPAT	OR	ON	2008/09/26 18:01
S6	332	S5 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/26 18:05
S7	91	S6 and ((base or bottom) with trench with (dop$3 or implant$5))	US-PGPUB; USPAT	OR	ON	2008/09/26 18:06

S8	8726	trench near5 transistor	US-PGPUB; USPAT	OR	ON	2008/09/26 22:02
S9	6573	S8 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/26 22:02
S10	3963	S9 and diffusion	US-PGPUB; USPAT	OR	ON	2008/09/26 22:02
S11	415	S10 and (p near3 n near3 junction)	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S12	141	S11 and ((base or bottom) with trench with (dop$3 or implant$5))	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S13	20422	insulated near3 gate with transistor	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S14	3657	S13 and trench	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S15	2406	S14 and diffusion	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S16	435	S15 and (p near3 n near3 junction)	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S17	332	S16 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S18	91	S17 and ((base or bottom) with trench with (dop$3 or implant$5))	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S19	114	S12 not S18	US-PGPUB; USPAT	OR	ON	2008/09/26 22:03
S20	36	steven with t with peake	US-PGPUB; USPAT	OR	ON	2008/09/26 22:37
S21	32	S20 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/26 22:37
S22	21	steven with t with peake	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/26 22:40
S23	2652	trench near3 (FET or MOSFET)	US-PGPUB; USPAT	OR	ON	2008/09/26 22:42
S24	1959	S23 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/26 22:42
S25	602	S24 and ((base or bottom) with trench with (dop$3 or implant$5))	US-PGPUB; USPAT	OR	ON	2008/09/26 22:42
S26	559	S25 not S18	US-PGPUB; USPAT	OR	ON	2008/09/26 22:43
S27	533	S26 not S19	US-PGPUB; USPAT	OR	ON	2008/09/26 22:43
S28	212	S27 and (low with (doping or impurity or density))	US-PGPUB; USPAT	OR	ON	2008/09/26 22:44
S29	11132	vertical near3 transistor	US-PGPUB; USPAT	OR	ON	2008/09/27 16:49
S30	2	S29 and (trench with (moat near3 etch$3))	US-PGPUB; USPAT	OR	ON	2008/09/27 16:50
S31	6107	trench near3 transistor	US-PGPUB; USPAT	OR	ON	2008/09/27 16:53
S32	8	S31 and (trench with (moat near3 etch$3))	US-PGPUB; USPAT	OR	ON	2008/09/27 16:53

S33	6	S32 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/27 16:53
S34	42	(trench with (moat near3 etch$3))	US-PGPUB; USPAT	OR	ON	2008/09/27 16:55
S35	31	S34 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/27 16:55
S36	3313	438/173,192,197,206,207,212.ccls.	US-PGPUB; USPAT	OR	ON	2008/09/27 17:39
S37	2434	S36 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2008/09/27 17:39
S38	150	S37 and ((base or bottom) with trench with (dop$3 or implant$5))	US-PGPUB; USPAT	OR	ON	2008/09/27 17:39
S39	0	dose with concention	US-PGPUB; USPAT	OR	ON	2009/03/20 15:23
S40	56572	dose with concentration	US-PGPUB; USPAT	OR	ON	2009/03/20 15:24
S41	42223	S40 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2009/03/20 15:24
S42	663	S41 and (low near3 (doped or doping))	US-PGPUB; USPAT	OR	ON	2009/03/20 15:24
S43	246	S42 and trench	US-PGPUB; USPAT	OR	ON	2009/03/20 15:24
S44	224	S43 and transistor	US-PGPUB; USPAT	OR	ON	2009/03/20 15:24
S45	37	S44 and (insulated with transistor)	US-PGPUB; USPAT	OR	ON	2009/03/20 15:25
S46	1	("20070141783").PN.	US-PGPUB; USPAT	OR	OFF	2009/03/20 15:58
S48	1638	trench adj (fet or transistor or mosfet)	US-PGPUB; USPAT	OR	ON	2009/03/29 22:07
S49	1181	S48 and @ad<"20050223"	US-PGPUB; USPAT	OR	ON	2009/03/29 22:08
S50	1002	S49 and (gate with trench)	US-PGPUB; USPAT	OR	ON	2009/03/29 22:08
S52	188	S50 and (p near3 n with junction)	US-PGPUB; USPAT	OR	ON	2009/03/29 22:09
S53	181	S52 and drain	US-PGPUB; USPAT	OR	ON	2009/03/29 22:11

3/30/09 9:05:02 AM
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